ABSTRACT

MEMORY DEVICE AND METHOD OF OPERATING THE SAME

Provided herein may be a memory device and a method of operating the same. The memory device may include a plurality of memory cells, a peripheral circuit, and a control logic. The memory cells may be coupled to a plurality of word lines. The peripheral circuit may perform a memory operation on selected memory cells. The control logic may control the peripheral circuit, during the memory operation, to apply an operating voltage to a selected word line, among the plurality of word lines, coupled to the selected memory cells, a first pass voltage to target word lines adjacent to the selected word line among unselected word lines, based on whether the operating voltage is lower than or equal to a reference voltage, and a second pass voltage, having a lower level than the first pass voltage, to remaining unselected word lines, other than the target word lines.

FIG. 2